

RF360 Europe GmbH
A Qualcomm – TDK Joint Venture

Data sheet

SAW multiplexer LTE band 1 + LTE band 3

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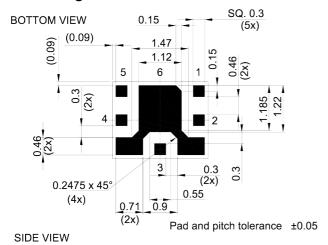
1 Application

- Low-loss SAW multiplexer for mobile telephone LTE Band 1 and Band 3 systems, also suitable for WCDMA applications.
- Usable pass bands: 60MHz for Band 1 and 75 MHz for Band 3.
- High out of band selectivity
- High TX-RX isolation
- Terminating impedance 50Ω
- Unbalanced to unbalanced operation

2 Features

- Package size 2.5±0.05 mm × 2.0±0.05 mm
- Package height 0.7 mm (max.)
- Approximate weight 8 mg
- RoHS compatible
- Package for Surface Mount Technology (SMT)
- Ni/Au-plated terminals
- Electrostatic Sensitive Device (ESD)
- Moisture Sensitivity Level 3 (MSL3)

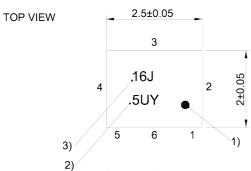
3 Package



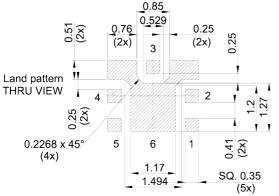
4 Pin configuration

- 1 TX (B1)
- 2 TX (B3)
- 3 ANT (B1 & B3)
- 4 RX (B1)
- 5 RX (B3)
- 6 Ground

✓ 0.03



- 1) Marking for pad number 1
- 2) Example of encoded lot number
- 3) Example of encoded filter type number



Landing pad tolerance -0.02

Figure 1: Drawing of package with package height A = 0.7 mm (max.). See Sec. Package information (p. 39).

5 Matching circuit

■ L_{p2b} = 8.5 nH

■ L_{p4} = 6.4 nH

■ L_{p5} = 12 nH

■
$$L_{s1}$$
 = 2.4 nH

■ L_{s2a} = 2.0 nH

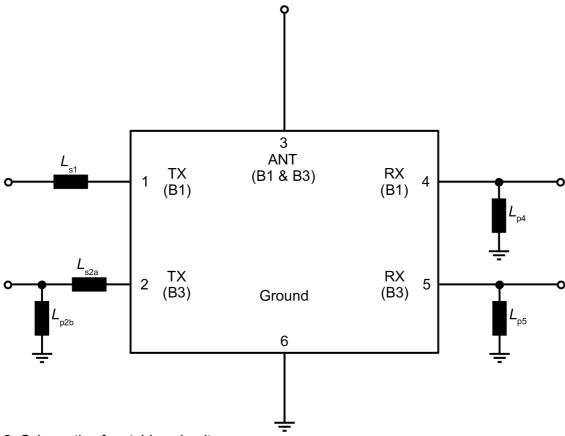


Figure 2: Schematic of matching circuit.

External shunt inductor for ESD protection is recommended at any ports towards antenna.

6 **Characteristics LTE B1**

TX - ANT 6.1

Temperature range for specification B1 TX terminating impedance ANT terminating impedance

B1 RX terminating impedance

= -30 °C ... +85 °C $Z_{\rm B1\,TX}$ = 50 Ω with ser. 2.4 nH¹⁾

= 50 Ω

= 50 Ω with par. 6.4 nH¹⁾

Characteristics LTE B1 TX – ANT				$\begin{array}{c} \text{min.} \\ \text{for } T_{\text{SPEC}} \end{array}$	typ. @ +25 °C	$\begin{array}{c} \text{max.} \\ \text{for } T_{\text{\tiny SPEC}} \end{array}$	
Maximum insertion attenuation			$\alpha_{\text{INT,max}}^{\qquad 2)}$				
	1920 1980	MHz	,	_	1.6 ³⁾	2.4	dB
Amplitude ripple (p-p)							
	1920.25 1979.75	MHz	$\Delta\alpha^{\scriptscriptstyle 4)}$	_	0.6	2.0	dB
	1920.25 1979.75	MHz	$\Delta\alpha^{5)}$	_	0.6	2.0	dB
Maximum VSWR			$VSWR_{max}$				
@ B1 TX port	1920.25 1979.75	MHz		_	1.4	2.0	
@ ANT port	1920.25 1979.75	MHz		_	1.3	2.0	
Minimum attenuation							
	10 1574	MHz	α_{min}	30	45	_	dB
	420 494	MHz	$\boldsymbol{\alpha}_{\text{min}}$		63	_	dB
	815 960	MHz	$\boldsymbol{\alpha}_{_{min}}$		51	_	dB
	1226 1250	MHz	$\alpha_{_{min}}$	43	47	_	dB
	1447.9 1462.9	MHz	$\boldsymbol{\alpha}_{\text{min}}$	30	45	_	dB
	1475 1511	MHz	α_{min}		45	_	dB
	1559 1607	MHz	$\alpha_{_{min}}$		45	_	dB
	1607 1710	MHz	α_{min}		36	_	dB
	1710.15 1784.85	MHz	α_{\min}		36	_	dB
	1805.15 1879.85	MHz	α _{min}		58	_	dB
	2010 2025	MHz	α _{min}		41	_	dB
	2110 2170	MHz	$lpha_{INT,min}^{min}$	48	59	_	dB
	2400 2500	MHz	α _{min}		51	_	dB
	2500 2690	MHz	α_{\min}	45	50	_	dB
	3830 3960	MHz			39	_	dB
			α_{min}			_	
	4900 5740	MHz	α_{min}	20	25	_	dB
	5740 5950	MHz	α_{min}	25	30	_	dB

¹⁾ See Sec. Matching circuit (p. 6).

²⁾ Integrated attenuation α_{INT} : Averaged power $|S_{ij}|^2$ over the center 4.5 MHz of LTE 5 MHz (25 RB) channels.

Typical value averaged over indicated frequency range.

Over any 5 MHz.

Over any channel with band width of 5 MHz.

Valid for temperature $T = +15 \,^{\circ}\text{C...} + 85 \,^{\circ}\text{C.}$



6.2 ANT - RX

Temperature range for specification $T_{\text{SPEC}} = -30 \,^{\circ}\text{C} \dots +85 \,^{\circ}\text{C}$ B1 TX terminating impedance $Z_{\text{B1 TX}} = 50 \,^{\circ}\Omega$ with ser. 2.4 nH¹⁾

ANT terminating impedance $Z_{ANT} = 50 \Omega$

B1 RX terminating impedance $Z_{B1 RX} = 50 \Omega$ with par. 6.4 nH¹⁾

Characteristics LTE B1 ANT – RX				$\begin{array}{c} \text{min.} \\ \text{for } T_{\text{SPEC}} \end{array}$	typ. @ +25 °C	$\begin{array}{c} \text{max.} \\ \text{for } T_{\text{\tiny SPEC}} \end{array}$	
Maximum insertion attenuation			α _{INT,max} ²⁾				
	2110 2170	MHz		_	1.6 ³⁾	2.4	dB
Amplitude ripple (p-p)							
	2110.25 2169.75	MHz	$\Delta\alpha^{\scriptscriptstyle 4)}$	_	0.5	1.5	dB
	2110.25 2169.75	MHz	$\Delta \alpha^{5)}$	_	0.5	1.5	dB
Maximum VSWR			$VSWR_{max}$				
@ ANT port	2110.25 2169.75	MHz		_	1.4	2.0	
@ B1 RX port	2110.25 2169.75	MHz		_	1.4	2.0	
Minimum attenuation							
	10 1920	MHz	$\boldsymbol{\alpha}_{\text{min}}$	37	42	_	dB
	190	MHz	$\boldsymbol{\alpha}_{\text{min}}$		101	_	dB
	718 748	MHz	$\boldsymbol{\alpha}_{_{min}}$		70	_	dB
	814 915	MHz	$\alpha_{_{min}}$	50	64	<u> </u>	dB
	1427 1447	MHz	$\boldsymbol{\alpha}_{\text{min}}$	40	52	_	dB
	1447 1463	MHz	$\boldsymbol{\alpha}_{min}$	45	52	_	dB
	1710.15 1784.85	MHz	$\boldsymbol{\alpha}_{\text{min}}$	48	59	<u> </u>	dB
	1920 1980	MHz	α _{INT,min} ²⁾	48	59	_	dB
	1980 2015	MHz	α_{min}	15	49	_	dB
	2015 2050	MHz	$\alpha_{_{min}}$	30	42	_	dB
	2050 2075	MHz	$\alpha_{_{min}}$	10	26	_	dB
	2255 2690	MHz	α _{min}	40	45	_	dB
	4030 4150	MHz	α _{min}	40	48	_	dB
	4220 4340	MHz	α _{min}		47	_	dB
	4340 5950	MHz	α _{min} α _{min}		40		dB

¹⁾ See Sec. Matching circuit (p. 6).

Integrated attenuation α_{INT} : Averaged power $|S_{ii}|^2$ over the center 4.5 MHz of LTE 5 MHz (25 RB) channels.

Typical value averaged over indicated frequency range.

Over any 5 MHz.

⁵⁾ Over any channel with band width of 5 MHz.



6.3 TX - RX

Temperature range for specification $T_{\rm SPEC} = -30~{\rm ^{\circ}C}~...~+85~{\rm ^{\circ}C}$ B1 TX terminating impedance $Z_{\rm B1\,TX} = 50~\Omega$ with ser. 2.4 nH¹¹ and the specification $Z_{\rm SMT} = 50~\Omega$

B1 RX terminating impedance $Z_{\text{B1 PY}} = 50 \Omega$ with par. 6.4 nH¹⁾

Characteristics LTE B1 TX – RX				$\begin{array}{c} \text{min.} \\ \text{for } T_{\text{SPEC}} \end{array}$	typ. @ +25 °C	$\begin{array}{c} \text{max.} \\ \text{for } T_{\text{\tiny SPEC}} \end{array}$	
Minimum isolation							
	1574 1577	MHz	$\boldsymbol{\alpha}_{_{min}}$	40	72	_	dB
	1805 1880	MHz	$\boldsymbol{\alpha}_{_{min}}$	40	67	_	dB
	1920 1980	MHz	$\alpha_{\text{INT,min}}^{ 2)}$	55	63	_	dB
	2110 2170	MHz	$\alpha_{\text{INT,min}}^{\qquad 2)}$	55	62	_	dB
	3830 3970	MHz	$\alpha_{_{min}}$	30	63	_	dB
	5750 5950	MHz	$\boldsymbol{\alpha}_{\text{min}}$	30	63	_	dB

¹⁾ See Sec. Matching circuit (p. 6).

Integrated attenuation α_{INT} : Averaged power $|S_{ii}|^2$ over the center 4.5 MHz of LTE 5 MHz (25 RB) channels.



7 **Characteristics LTE B3**

TX - ANT 7.1

= -30 °C ... +85 °C Temperature range for specification

 $Z_{\rm B3\,TX}$ B3 TX terminating impedance = 50 Ω with par. 8.5 nH & ser. 2.0 nH¹⁾

 $Z_{\scriptscriptstyle{\mathrm{ANT}}}$ = 50 Ω ANT terminating impedance

= 50 Ω with par. 12 nH¹⁾ B3 RX terminating impedance

Characteristics LTE B3 TX – ANT				$\begin{array}{c} \text{min.} \\ \text{for } T_{\text{SPEC}} \end{array}$	typ. @ +25 °C	$\begin{array}{c} \text{max.} \\ \text{for } T_{\text{SPEC}} \end{array}$	
Maximum insertion attenuation			$\alpha_{\text{INT,max}}^{\qquad 2)}$				
	1710 1785	MHz		_	1.73)	3.2	dB
Amplitude ripple (p-p)							
	1710.15 1784.85	MHz	$\Delta \alpha^{\scriptscriptstyle 4)}$	_	1.2	2.0	dB
	1710.15 1784.85	MHz	$\Delta \alpha^{5)}$	_	1.2	2.0	dB
Maximum VSWR			$VSWR_{max}$				
@ B3 TX port	1710.15 1784.85	MHz		_	1.4	2.0	
@ ANT port	1710.15 1784.85	MHz		_	1.5	2.0	
Minimum attenuation							
	10 1566	MHz	$\boldsymbol{\alpha}_{min}$	40	45	_	dB
	703 960	MHz	$\boldsymbol{\alpha}_{min}$	44	53	_	dB
	1226 1250	MHz	$\boldsymbol{\alpha}_{\text{min}}$	43	47	_	dB
	1496 1511	MHz	$\alpha_{_{min}}$	_	45	_	dB
	1559 1607	MHz	$\boldsymbol{\alpha}_{\text{min}}$	43	49	_	dB
	1805 1880	MHz	$\alpha_{\text{INT,min}}^{}2)}$		58	_	dB
	1920.25 1979.75	MHz	$\alpha_{_{min}}$	30	39	_	dB
	2110.25 2169.75	MHz	$\boldsymbol{\alpha}_{\text{min}}$		55	_	dB
	2400 2690	MHz	$\boldsymbol{\alpha}_{\text{min}}$		39	_	dB
	3420 3570	MHz	$\alpha_{_{min}}$		34	_	dB
	4900 5950	MHz	$\alpha_{_{min}}$		33	_	dB
	6840 7140	MHz	$\boldsymbol{\alpha}_{_{min}}$	15	26	_	dB

See Sec. Matching circuit (p. 6). Integrated attenuation α_{INT} : Averaged power $|S_{ij}|^2$ over the center 4.5 MHz of LTE 5 MHz (25 RB) channels.

Typical value averaged over indicated frequency range.

Over any 5 MHz.

Over any channel with band width of 5 MHz.



7.2 ANT - RX

Temperature range for specification $T_{\text{SPEC}} = -30 \,^{\circ}\text{C} \dots +85 \,^{\circ}\text{C}$

B3 TX terminating impedance $Z_{B3 TX} = 50 \Omega$ with par. 8.5 nH & ser. 2.0 nH¹⁾

ANT terminating impedance $Z_{\text{ANT}} = 50 \ \Omega$

B3 RX terminating impedance $Z_{B3 RX} = 50 \Omega$ with par. 12 nH¹⁾

Characteristics LTE B3 ANT – RX				$\begin{array}{c} \text{min.} \\ \text{for } T_{\text{SPEC}} \end{array}$	typ. @ +25 °C	$\begin{array}{c} \text{max.} \\ \text{for } T_{\text{\tiny SPEC}} \end{array}$	
Maximum insertion attenuation			α _{INT,max} ²⁾				
	1805 1880	MHz	,	_	1.74)	3.4 ³⁾	dB
	1805 1880	MHz		_	1.74)	4.0	dB
Amplitude ripple (p-p)							
	1805.15 1879.85	MHz	$\Delta\alpha^{5)}$	_	1.4	2.0	dB
	1805.15 1879.85	MHz	$\Delta\alpha^{6)}$	–	1.4	2.0	dB
Maximum VSWR			$VSWR_{max}$				
@ ANT port	1805.15 1879.85	MHz		_	1.7	2.0	
@ B3 RX port	1805.15 1879.85	MHz		_	1.7	2.0	
Minimum attenuation							
	10 1710	MHz	$\boldsymbol{\alpha}_{\text{min}}$	35	47	_	dB
	95	MHz	α_{min}	50	106	_	dB
	718 915	MHz	$\boldsymbol{\alpha}_{\text{min}}$	45	59	_	dB
	1447 1463	MHz	$\boldsymbol{\alpha}_{\text{min}}$	40	49	_	dB
	1615 1690	MHz	$\boldsymbol{\alpha}_{\text{min}}$	40	49	_	dB
	1710 1785	MHz	$\alpha_{\text{INT,min}}^{\qquad 2)}$	45	54	_	dB
	1785 1790	MHz	α_{min}	30 ⁷⁾	33	_	dB
	1785 1790	MHz	α_{min}		33	_	dB
	1920.25 1979.75	MHz	α_{min}		57	_	dB
	1980 2400	MHz	$\alpha_{_{min}}$	35	42	_	dB
	2400 2570	MHz	$\alpha_{_{ m min}}$	38	44	_	dB
	2570 3515	MHz	α _{min}	38	44	_	dB
	3515 3665	MHz	min α _{min}		43	_	dB
	3665 3760	MHz	α_{\min}	35	43	_	dB
	3760 4900	MHz	α_{\min}	30	41	_	dB
	4900 5950	MHz	α_{\min}	30	40		dB

¹⁾ See Sec. Matching circuit (p. 6).

Integrated attenuation $\alpha_{|NT|}$: Averaged power $|S_{ij}|^2$ over the center 4.5 MHz of LTE 5 MHz (25 RB) channels.

³⁾ Valid for typical temperature T = +25 °C.

⁴⁾ Typical value averaged over indicated frequency range.

⁵⁾ Over any 5 MHz.

⁶⁾ Over any channel with band width of 5 MHz.

Valid for temperature $T = -30 \,^{\circ}\text{C...} + 25 \,^{\circ}\text{C.}$



7.3 TX - RX

Temperature range for specification $T_{\text{SPEC}} = -30 \,^{\circ}\text{C} \dots +85 \,^{\circ}\text{C}$

B3 TX terminating impedance $Z_{B3 TX} = 50 \Omega$ with par. 8.5 nH & ser. 2.0 nH¹⁾

ANT terminating impedance $Z_{ANT} = 50 \Omega$

B3 RX terminating impedance $Z_{\text{\tiny B3 PY}} = 50 \,\Omega$ with par. 12 nH¹⁾

Characteristics LTE B3 TX – RX				$\begin{array}{c} \text{min.} \\ \text{for } T_{\text{SPEC}} \end{array}$	typ. @ +25 °C	$\begin{array}{c} \text{max.} \\ \text{for } T_{\text{\tiny SPEC}} \end{array}$	
Minimum isolation							
	1710 1785	MHz	$\alpha_{\text{INT,min}}^{\qquad 2)}$	51	55	_	dB
	1805 1880	MHz	$\alpha_{\text{INT,min}}^{\qquad 2)}$	55	60	_	dB
	2110.25 2169.75	MHz	α_{min}	40	64	_	dB

¹⁾ See Sec. Matching circuit (p. 6).

Integrated attenuation α_{INT} : Averaged power $|S_{ij}|^2$ over the center 4.5 MHz of LTE 5 MHz (25 RB) channels.



8 Cross-isolations

8.1 LTE B1 TX - LTE B3 RX

Temperature range for specification $T_{\rm SPEC} = -30~{\rm ^{\circ}C}~...~+85~{\rm ^{\circ}C}$ B1 TX terminating impedance $Z_{\rm B1~TX} = 50~\Omega$ with ser. 2.4 nH¹⁾ B3 RX terminating impedance $Z_{\rm B3~RX} = 50~\Omega$ with par. 12 nH¹⁾

Characteristics cross-isolation LTE B1 TX – LTE B3 RX				$\begin{array}{c} \text{min.} \\ \text{for } T_{\text{SPEC}} \end{array}$	typ. @ +25 °C	$\begin{array}{c} \text{max.} \\ \text{for } T_{\text{\tiny SPEC}} \end{array}$	
Minimum cross-isolation			$\alpha_{\text{INT,min}}^{\qquad 2)}$				
	1805 1880	MHz		55	61	_	dB
	1920 1980	MHz		54	58	_	dB

See Sec. Matching circuit (p. 6).

Integrated attenuation α_{INT} : Averaged power $|S_{ij}|^2$ over the center 4.5 MHz of LTE 5 MHz (25 RB) channels.



8.2 LTE B3 TX - LTE B1 RX

Temperature range for specification $T_{\text{SPEC}} = -30 \,^{\circ}\text{C} \dots +85 \,^{\circ}\text{C}$

B3 TX terminating impedance $Z_{B3 TX} = 50 \Omega$ with par. 8.5 nH & ser. 2.0 nH¹⁾

B1 RX terminating impedance $Z_{\text{px,px}} = 50 \Omega$ with par. 6.4 nH¹⁾

Characteristics cross-isolation LTE B3 TX – LTE B1 RX				$\begin{array}{c} \text{min.} \\ \text{for } T_{\text{SPEC}} \end{array}$	typ. @ +25 °C	$\begin{array}{c} \text{max.} \\ \text{for } T_{\text{\tiny SPEC}} \end{array}$	
Minimum cross-isolation			$\alpha_{\text{INT,min}}^{\qquad 2)}$				
	1710 1785	MHz		55	60	_	dB
	2110 2170	MHz		55	62	_	dB

¹⁾ See Sec. Matching circuit (p. 6).

Integrated attenuation α_{INT} : Averaged power $|S_i|^2$ over the center 4.5 MHz of LTE 5 MHz (25 RB) channels.



9 **Maximum ratings**

Operable temperature	T _{OP} = -30 °C +85 °C	
Storage temperature	T _{STG} ¹⁾ = −40 °C +85 °C	
DC voltage	$ V_{DC} ^{2)} = 0 \text{ V (max.)}$	
ESD voltage		
	$V_{\rm ESD}^{3)} = 50 \text{ V (max.)}$	Machine model.
	$V_{\rm ESD}^{4)} = 350 \rm V (max.)$	Human body model.
	$V_{\rm ESD}^{5)} = 1000 \rm V (max.)$	Charged device model.
Input power	P _{IN}	
@ B1 TX port: 1920.25 1979.75 MHz	30 dBm	Continuous wave for 5000 h @ 50 °C.
@ B1 RX port: 2110.25 2169.75 MHz	10 dBm	Continuous wave for 5000 h @ 50 °C.
@ B3 TX port: 1710.15 1784.85 MHz	30 dBm	Continuous wave for 5000 h @ 50 °C.
@ B3 RX port: 1805.15 1879.85 MHz	10 dBm	Continuous wave for 5000 h @ 50 °C.

¹⁾ Not valid for packaging material. Storage temperature for packaging material is -25 °C to +40 °C.

²⁾ In case of applied DC voltage blocking capacitors are mandatory.

³⁾ According to JESD22-A115B (MM – Machine Model), 10 negative & 10 positive pulses.

According to JESD22-A114F (HBM – Human Body Model), 1 negative & 1 positive pulse.

According to JESD22-C101C (CDM – Field Induced Charged Device Model), 3 negative & 3 positive pulses.

10 Transmission coefficients LTE B1

10.1 TX - ANT 0.0 1.0 2.0 1.606 1.999 3.0 4.0 5.0 1900 1920 2000 19'40 1960 1980 f/MHz0.0 20.0 40.0 60.0 80.0 <u>+ .</u> 1800 2000 2200 1900 2100 2300 f/MHz 0.0 20.0 40.0 60.0

Figure 3: Attenuation TX – ANT.

1000

2000

80.0

3000

4000

6000

5000

f/MHz

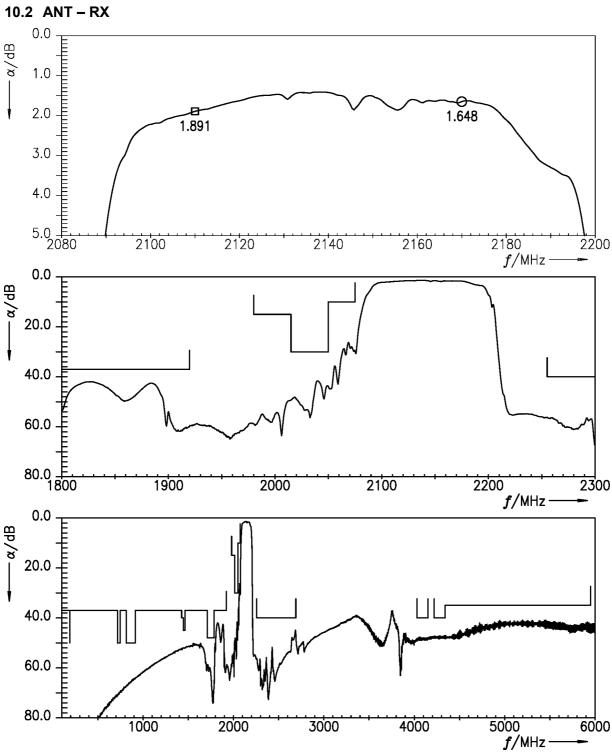


Figure 4: Attenuation ANT – RX.

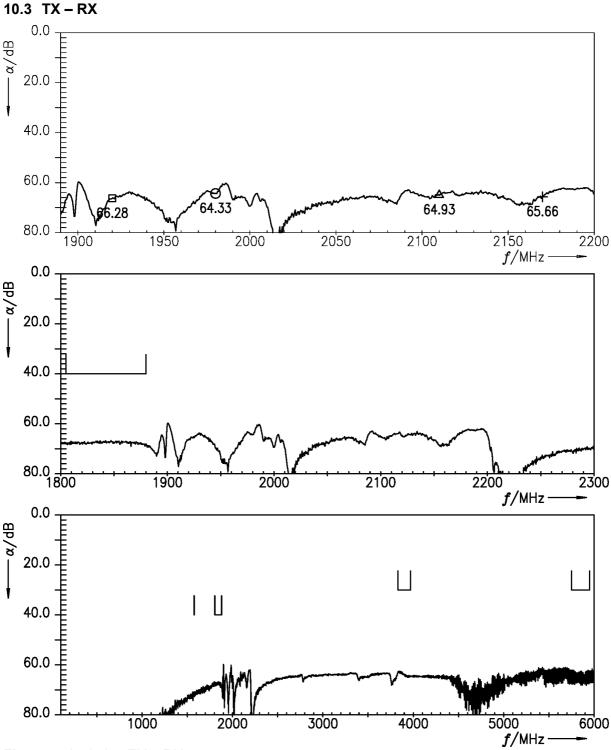


Figure 5: Isolation TX – RX.

11 Transmission coefficients (LTE) LTE B1

11.1 TX – ANT

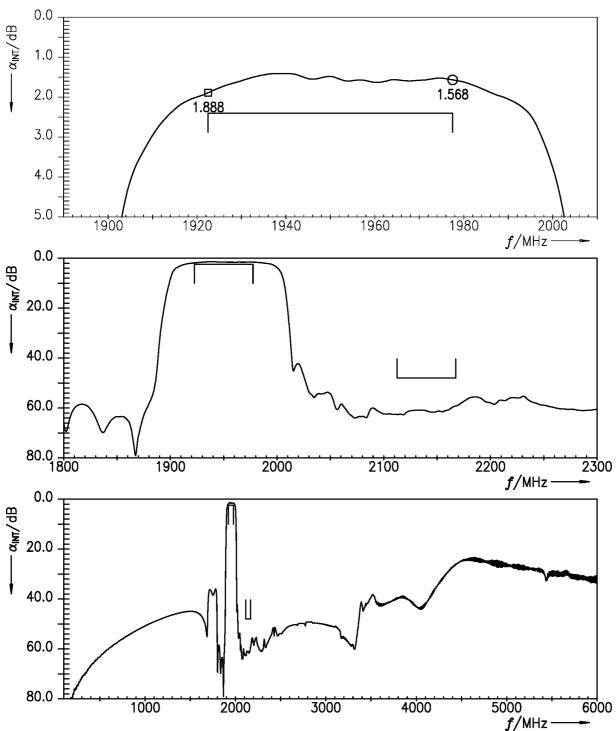


Figure 6: Attenuation (LTE) (integration window = 5 MHz) TX – ANT.

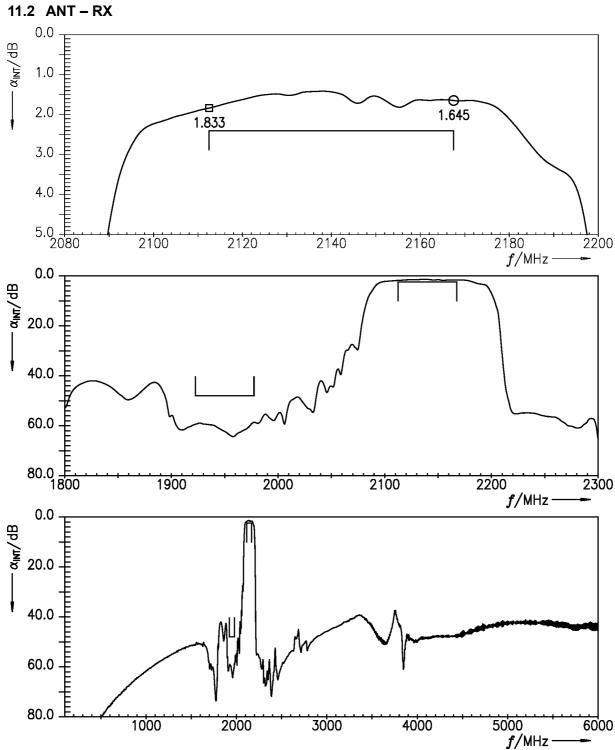


Figure 7: Attenuation (LTE) (integration window = 5 MHz) ANT – RX.

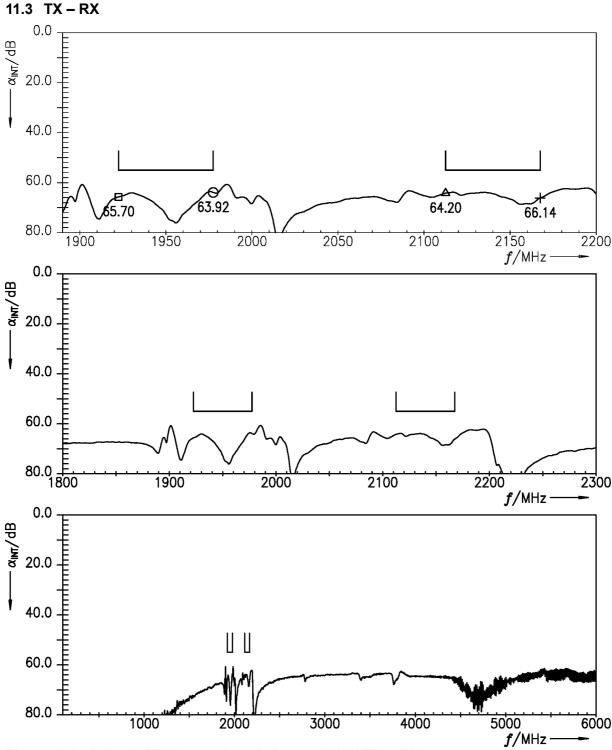
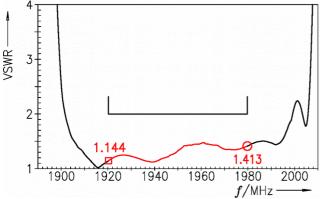


Figure 8: Isolation (LTE) (integration window = 5 MHz) TX – RX.

12 Reflection coefficients LTE B1



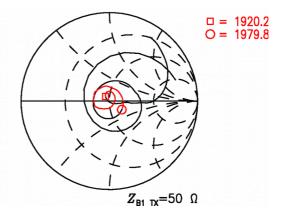
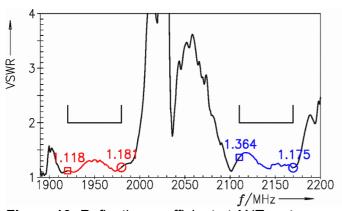


Figure 9: Reflection coefficient at B1 TX port.



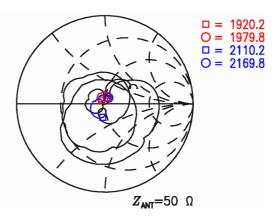
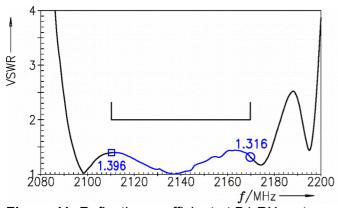


Figure 10: Reflection coefficient at ANT port.



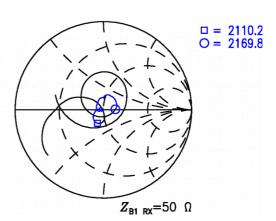


Figure 11: Reflection coefficient at B1 RX port.

13 Transmission coefficients LTE B3

13.1 TX - ANT

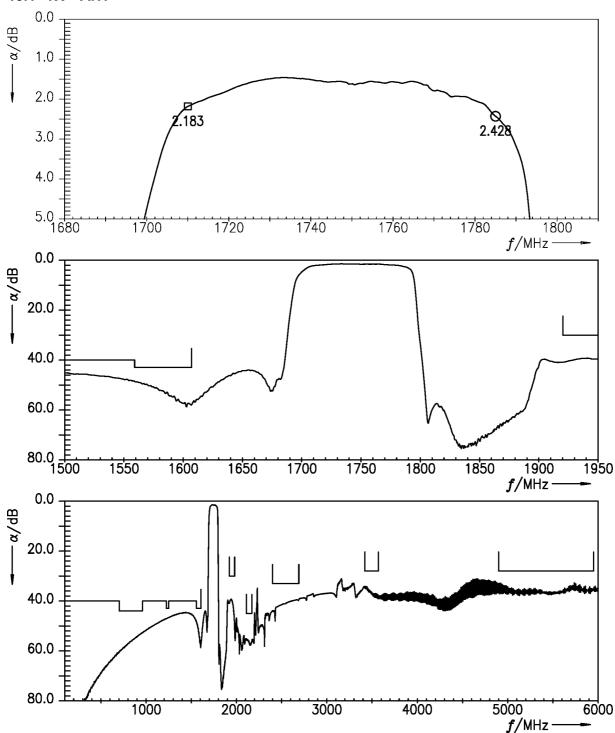


Figure 12: Attenuation TX – ANT.

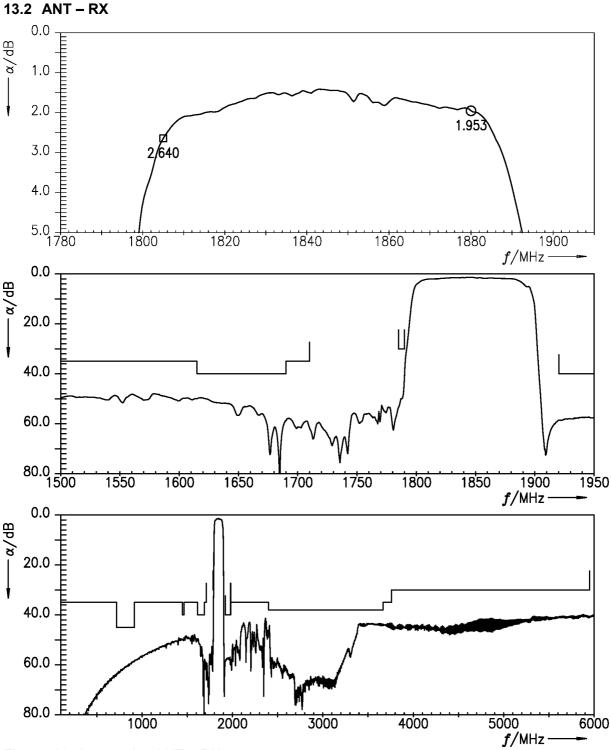


Figure 13: Attenuation ANT – RX.

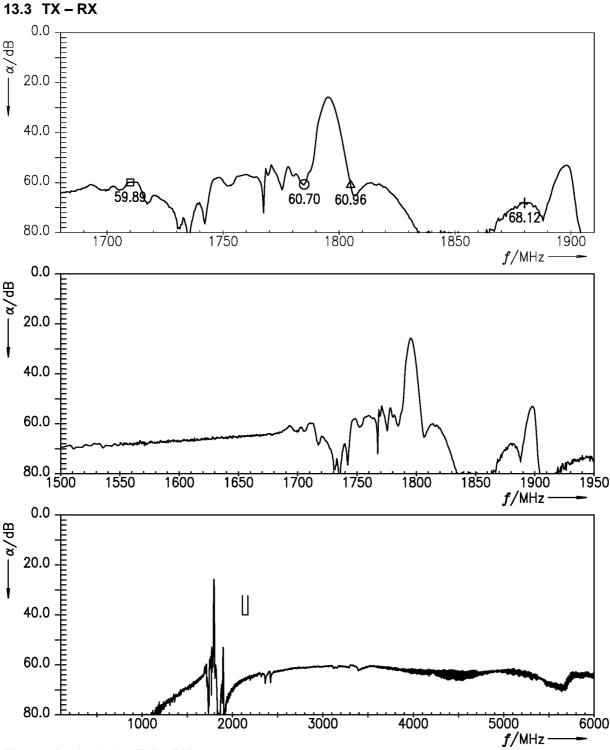


Figure 14: Isolation TX – RX.

14 Transmission coefficients (LTE) LTE B3

14.1 TX - ANT

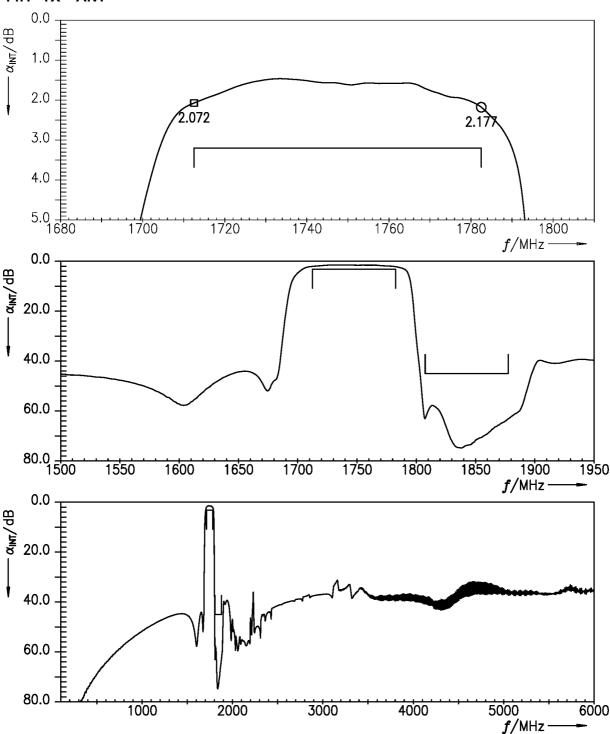


Figure 15: Attenuation (LTE) (integration window = 5 MHz) TX – ANT.

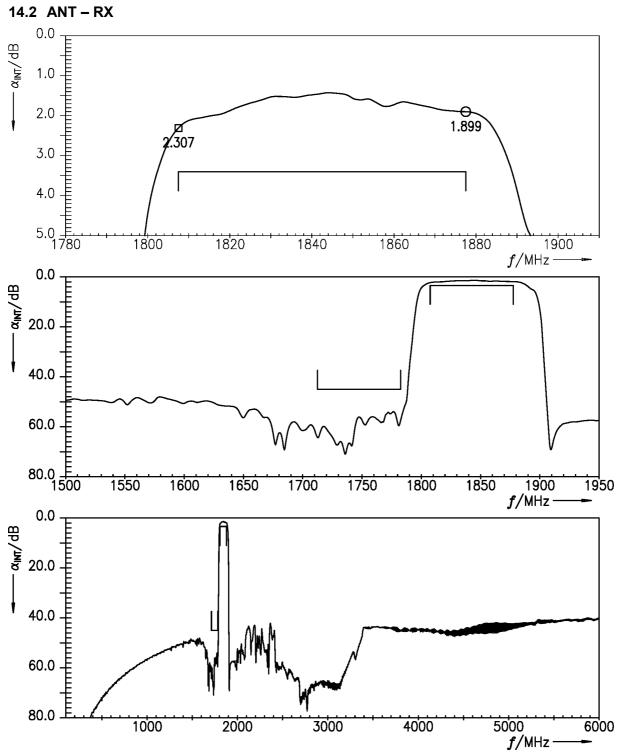


Figure 16: Attenuation (LTE) (integration window = 5 MHz) ANT – RX.

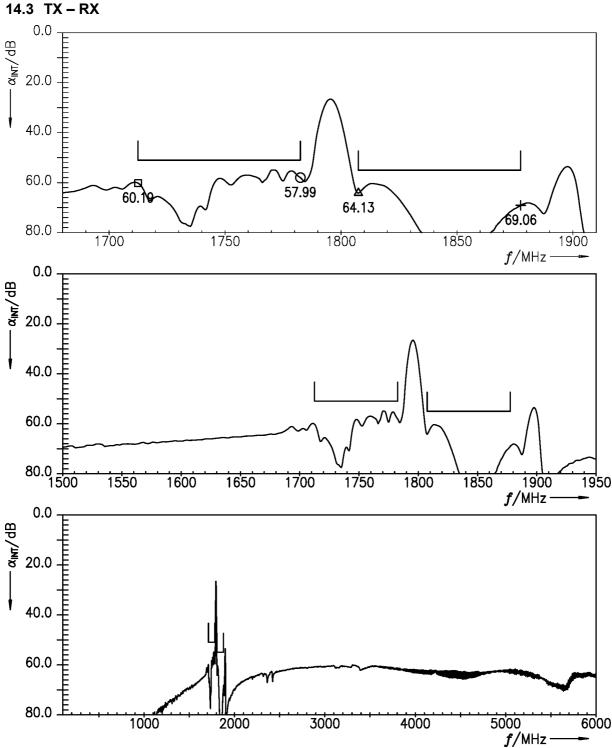
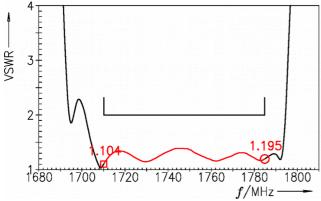


Figure 17: Isolation (LTE) (integration window = 5 MHz) TX – RX.

15 Reflection coefficients LTE B3



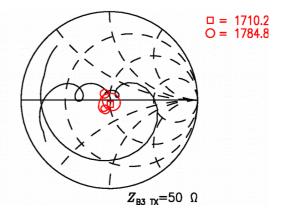
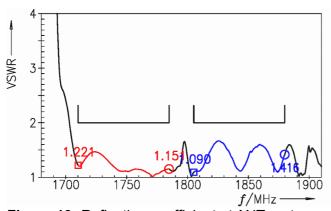


Figure 18: Reflection coefficient at B3 TX port.



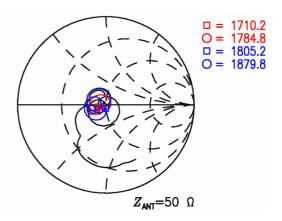
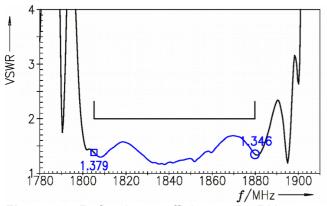


Figure 19: Reflection coefficient at ANT port.



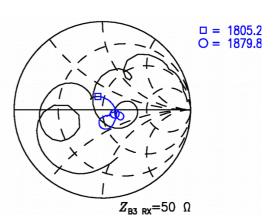


Figure 20: Reflection coefficient at B3 RX port.

16 Transmission coefficients (LTE) cross-isolations

16.1 LTE B1 TX - LTE B3 RX

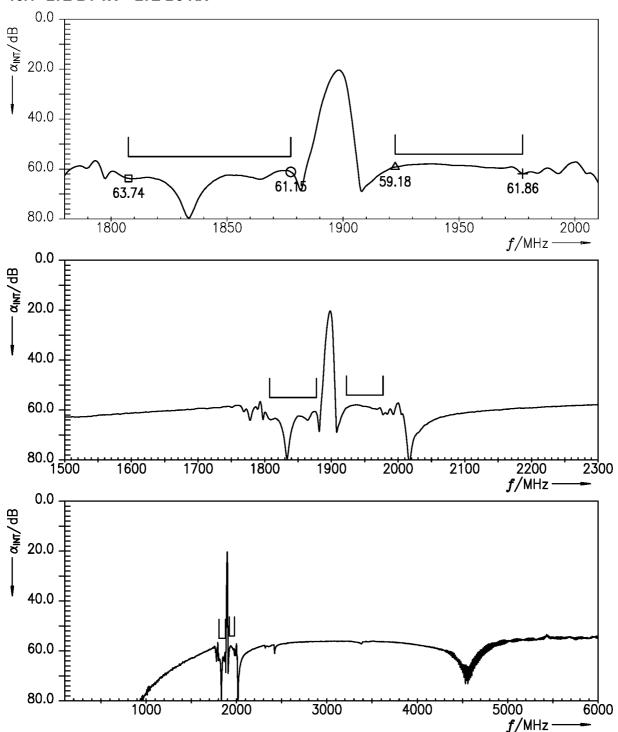


Figure 21: Cross-isolation (LTE) (integration window = 5 MHz) LTE B1 TX – LTE B3 RX.

16.2 LTE B3 TX - LTE B1 RX

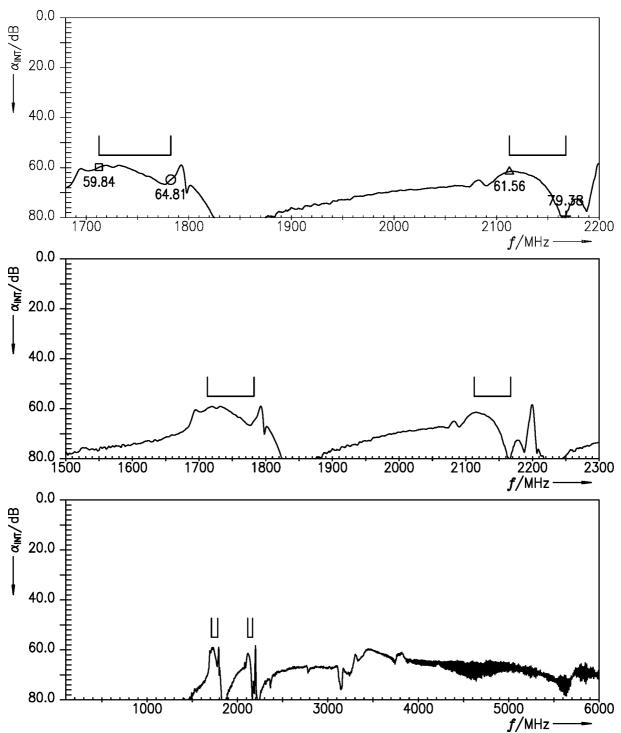


Figure 22: Cross-isolation (LTE) (integration window = 5 MHz) LTE B3 TX – LTE B1 RX.

17 Packing material

17.1 Tape

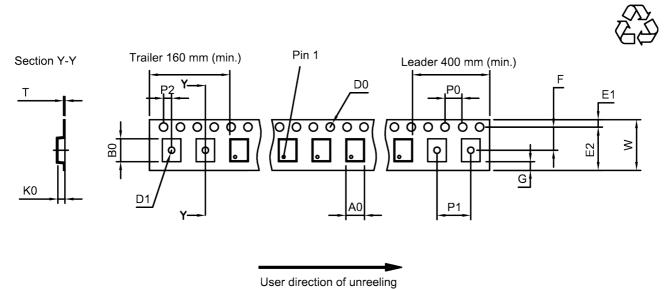


Figure 23: Drawing of tape (first-angle projection) for illustration only and not to scale. The valid tape dimensions are listed in Table 1.

A ₀	2.3±0.05 mm	E ₂	6.25 mm (min.)	P ₁	4.0±0.1 mm
B ₀	2.8±0.05 mm	F	3.5±0.05 mm	P ₂	2.0±0.05 mm
D_0	1.5+0.1/-0 mm	G	0.75 mm (min.)	Т	0.25±0.03 mm
D ₁	1.0 mm (min.)	K ₀	0.85±0.05 mm	W	8.0+0.3/-0.1 mm
E ₁	1.75 _{±0.1} mm	P ₀	4.0±0.1 mm		

Table 1: Tape dimensions.

17.2 Reel with diameter of 180 mm

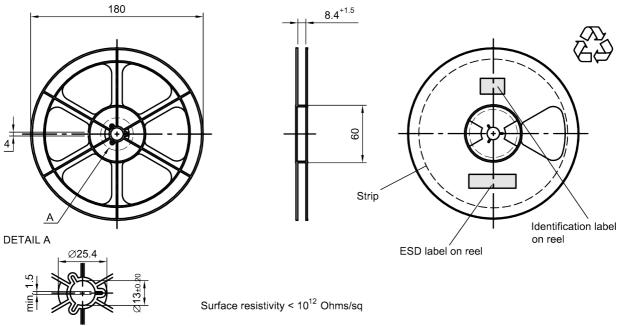


Figure 24: Drawing of reel (first-angle projection) with diameter of 180 mm.

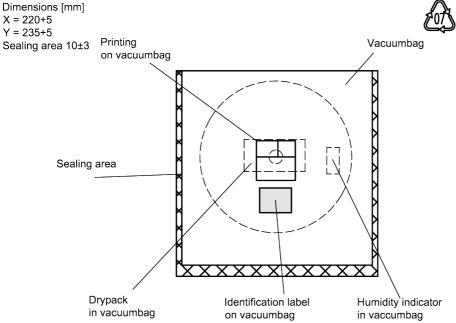


Figure 25: Drawing of moisture barrier bag (MBB) for reel with diameter of 180 mm.

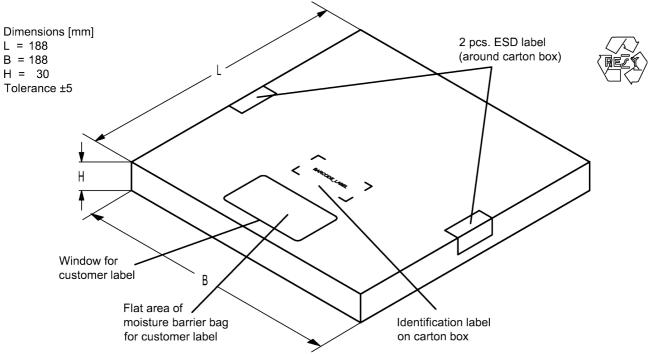


Figure 26: Drawing of folding box for reel with diameter of 180 mm.

17.3 Reel with diameter of 330 mm

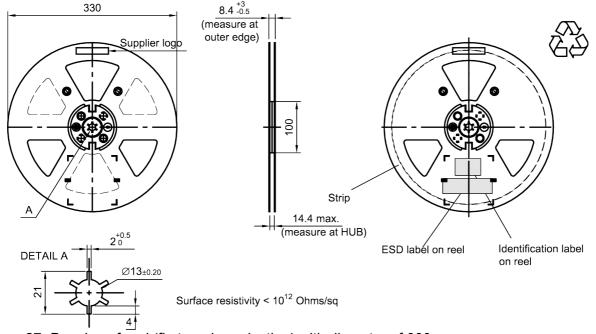


Figure 27: Drawing of reel (first-angle projection) with diameter of 330 mm.

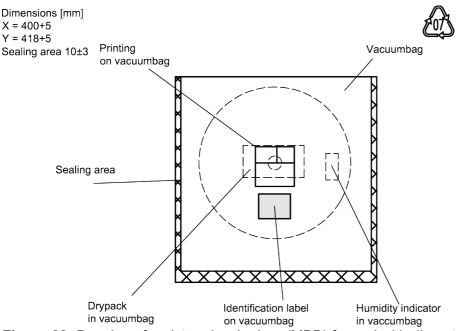


Figure 28: Drawing of moisture barrier bag (MBB) for reel with diameter of 330 mm.

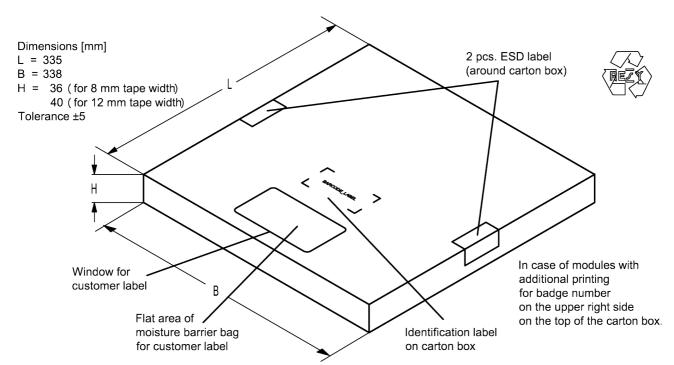


Figure 29: Drawing of folding box for reel with diameter of 330 mm.



18 Marking

Products are marked with product type number and lot number encoded according to Table 2:

■ Type number:

The 4 digit type number of the ordering code, e.g., B3xxxxB**1234**xxxx, is encoded by a special BASE32 code into a 3 digit marking.

Example of decoding type number marking on device in decimal code.

16J => 1234 1 x 32^2 + 6 x 32^1 + 18 (=J) x 32^0 = 1234

The BASE32 code for product type B8912 is 8PG.

■ Lot number:

The last 5 digits of the lot number, e.g., are encoded based on a special BASE47 code into a 3 digit marking.

Example of decoding lot number marking on device in decimal code.

5UY => 12345 $5 \times 47^2 + 27 (=U) \times 47^1 + 31 (=Y) \times 47^0 =$ 12345

Adopte	ed BASE32 co	ode for type r	number
Decimal	Base32	Decimal	Base32
value	code	value	code
0	0	16	G
1	1	17	Н
2	2	18	J
3	3	19	K
4	4	20	M
5	5	21	N
6	6	22	Р
7	7	23	Q
8	8	24	R
9	9	25	S
10	Α	26	Т
11	В	27	V
12	С	28	W
13	D	29	X
14	E	30	Y
15	F	31	Z

Adopted BASE47 code for lot number				
Decimal	Base47	Decimal	Base47	
value	code	value	code	
0	0	24	R	
1	1	25	S	
2	2	26	Т	
3	3	27	U	
4	4	28	V	
5	5	29	W	
6	6	30	X	
7	7	31	Y	
8	8	32	Z	
9	9	33	b	
10	Α	34	d	
11	В	35	f	
12	С	36	h	
13	D	37	n	
14	E	38	r	
15	F	39	t	
16	G	40	V	
17	Н	41	\	
18	J	42	?	
19	K	43	{	
20	L	44	}	
21	М	45	<	
22	Z	46	>	
23	Р			

Table 2: Lists for encoding and decoding of marking.

19 Soldering profile

The recommended soldering process is in accordance with IEC $60068-2-58-3^{rd}$ edit and IPC/JEDEC J-STD-020B.

ramp rate	≤ 3 K/s	
preheat	125 °C to 220 °C, 150 s to 210 s, 0.4 K/s to 1.0 K/s	
T > 220 °C	30 s to 70 s	
T > 230 °C	min. 10 s	
T > 245 °C	max. 20 s	
<i>T</i> ≥ 255 °C	-	
peak temperature T_{peak}	250 °C +0/-5 °C	
wetting temperature T_{\min}	230 °C +5/-0 °C for 10 s ± 1 s	
cooling rate	≤ 3 K/s	
soldering temperature T	measured at solder pads	

Table 3: Characteristics of recommended soldering profile for lead-free solder (Sn95.5Ag3.8Cu0.7).

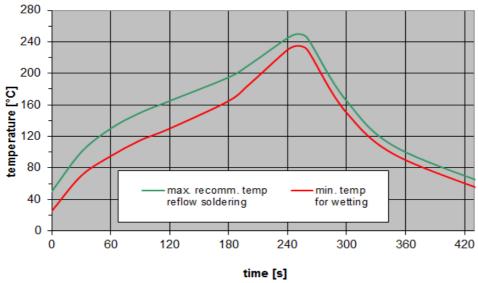


Figure 30: Recommended reflow profile for convection and infrared soldering – lead-free solder.



20 Annotations

20.1 RoHS compatibility

ROHS-compatible means that products are compatible with the requirements according to Art. 4 (substance restrictions) of Directive 2011/65/EU of the European Parliament and of the Council of June 8th, 2011, on the restriction of the use of certain hazardous substances in electrical and electronic equipment ("Directive") with due regard to the application of exemptions as per Annex III of the Directive in certain cases.

20.2 Scattering parameters (S-parameters)

The pin/port assignment is available in the headers of the S-parameter files. Please contact your local RF360 sales office.

20.3 Ordering codes and packing units

Ordering code	Packing unit
B39212B8912L210	15000 pcs
B39212B8912L210S 5	5000 pcs

Table 4: Ordering codes and packing units.



21 Cautions and warnings

21.1 Display of ordering codes for RF360 products

The ordering code for one and the same product can be represented differently in data sheets, data books, other publications and the website of RF360, or in order-related documents such as shipping notes, order confirmations and product labels. The varying representations of the ordering codes are due to different processes employed and do not affect the specifications of the respective products. Detailed information can be found on the Internet under www.rf360jv.com/orderingcodes.

21.2 Material information

Due to technical requirements components may contain dangerous substances. For information on the type in question please also contact one of our sales offices.

For information on recycling of tapes and reels please contact one of our sales offices.

21.3 Moldability

Before using in overmolding environment, please contact your local RF360 sales office.

21.4 Package information

Landing area

The printed circuit board (PCB) land pattern (landing area) shown is based on RF360 internal development and empirical data and illustrated for example purposes, only. As customers' SMD assembly processes may have a plenty of variants and influence factors which are not under control or knowledge of RF360, additional careful process development on customer side is necessary and strongly recommended in order to achieve best soldering results tailored to the particular customer needs.

Dimensions

Unless otherwise specified all dimensions are understood using unit millimeter (mm).

Projection method

Unless otherwise specified first-angle projection is applied.



22 Important notes

The following applies to all products named in this publication:

- 1. Some parts of this publication contain statements about the suitability of our products for certain areas of application. These statements are based on our knowledge of typical requirements that are often placed on our products in the areas of application concerned. We nevertheless expressly point out that such statements cannot be regarded as binding statements about the suitability of our products for a particular customer application. As a rule, RF360 Europe GmbH and its affiliates are either unfamiliar with individual customer applications or less familiar with them than the customers themselves. For these reasons, it is always ultimately incumbent on the customer to check and decide whether an RF360 product with the properties described in the product specification is suitable for use in a particular customer application.
- 2. We also point out that in individual cases, a malfunction of electronic components or failure before the end of their usual service life cannot be completely ruled out in the current state of the art, even if they are operated as specified. In customer applications requiring a very high level of operational safety and especially in customer applications in which the malfunction or failure of an electronic component could endanger human life or health (e.g. in accident prevention or life-saving systems), it must therefore be ensured by means of suitable design of the customer application or other action taken by the customer (e.g. installation of protective circuitry or redundancy) that no injury or damage is sustained by third parties in the event of malfunction or failure of an electronic component.
- 3. The warnings, cautions and product-specific notes must be observed.
- 4. In order to satisfy certain technical requirements, some of the products described in this publication may contain substances subject to restrictions in certain jurisdictions (e.g. because they are classed as hazardous). Useful information on this will be found in our Material Data Sheets on the Internet (www.rf360jv.com/material). Should you have any more detailed questions, please contact our sales offices.
- 5. We constantly strive to improve our products. Consequently, the products described in this publication may change from time to time. The same is true of the corresponding product specifications. Please check therefore to what extent product descriptions and specifications contained in this publication are still applicable before or when you place an order. We also reserve the right to discontinue production and delivery of products. Consequently, we cannot guarantee that all products named in this publication will always be available.

The aforementioned does not apply in the case of individual agreements deviating from the foregoing for customer-specific products.

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